

## Claims

1. A  $\text{SrRuO}_3$  conductive oxide sintered body characterized in that the relative density is 93% or more.
- 5 2. A conductive oxide sintered body according to claim 1, characterized in that the resistivity is  $500 \mu \Omega \text{ cm}$  or less.
3. A conductive oxide sintered body according to claim 1, characterized in that the resistivity is  $300 \mu \Omega \text{ cm}$  or less.
4. A conductive oxide sintered body according to each of claims 1 to 3, characterized in  
10 containing 0.3mol to 1.2mol of  $\text{Bi}_2\text{O}_3$ .
5. A conductive oxide sintered body according to each of claims 1 to 3, characterized in containing 0.5mol (and above) to 1.0mol of  $\text{Bi}_2\text{O}_3$ .
6. A sputtering target formed from a  $\text{SrRuO}_3$  conductive oxide sintered body characterized in that the relative density is 93% or more.
- 15 7. A sputtering target formed from a conductive oxide sintered body according to claim 6, characterized in that the resistivity is  $500 \mu \Omega \text{ cm}$  or less.
8. A sputtering target formed from a conductive oxide sintered body according to claim 6, characterized in that the resistivity is  $300 \mu \Omega \text{ cm}$  or less.
9. A sputtering target formed from a conductive oxide sintered body according to each of  
20 claims 6 to 8, characterized in containing 0.3mol to 1.2mol of  $\text{Bi}_2\text{O}_3$ .
10. A sputtering target formed from a conductive oxide sintered body according to each of claims 6 to 8, characterized in containing 0.5mol (and above) to 1.0mol of  $\text{Bi}_2\text{O}_3$ .
11. A manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering target formed from said sintered body, characterized in that 0.3mol to 1.2mol of  $\text{Bi}_2\text{O}_3$  is  
25 added as a sintering auxiliary upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body.
12. A manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering target formed from said sintered body, characterized in that 0.5mol (and above) to 1.0mol of  $\text{Bi}_2\text{O}_3$  is added as a sintering auxiliary upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body.
- 30 13. A manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering

target formed from said sintered body, characterized in that sintering is performed at a sintering temperature of 1400 to 1700°C upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body.

14. A manufacturing method of a  $\text{SrRuO}_3$  conductive oxide sintered body or a sputtering  
5 target formed from said sintered body according to claim 11 or claim 12, characterized in that sintering is performed at a sintering temperature of 1400 to 1700°C upon manufacturing the  $\text{SrRuO}_3$  conductive oxide sintered body.